

Substitute Form PTO-1449

U.S. Department of Commerce  
Patent and Trademark OfficeAttorney's Docket No.  
07977-004002Application No.  
New Continuation  
Application 10 602262**Information Disclosure Statement  
by Applicant**

(Use several sheets if necessary)

Applicant  
Naoto Kusumoto et al.Filing Date  
June 25, 2003Group Art Unit  
2828**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>Drfa</i>	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	AE	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			
	AG	5,365,875	11/1994	Asai et al.			
	AH	5,424,244	6/13/95	Zhang, et al.			
	AI	5,432,122	07/1995	Chae			
	AJ	5,477,073	12/1995	Wakai et al.			
	AK	5,496,768	03/1996	Kudo			
	AL	5,561,081	02/1994	Takenouchi et al.			
	AM	5,591,668	01/1997	Maegawa et al.			
	AN	5,643,801	7/1/97	Ishihara, et al.			
	AO	5,795,795	8/18/98	Kousai, et al.			
	AP	5,849,043	12/15/98	Zhang, et al.			
	AQ	5,891,764	4/6/99	Ishihara, et al.			
	AR	5,897,799	4/27/99	Yamazaki et al.			
	AS	6,143,661	11/7/2000	Kousai, et al.			
<i>Drfa</i>	AT	6,358,784	03/19/2002	Zhang, et al.			

**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<i>Drfa</i>	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
<i>Drfa</i>	AX	3-286518	12/1991	Japan				


Examiner's Signature

Date Considered

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Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 07977-004002		Application No. New Continuation Application 10-602762	
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)				Applicant Naoto Kusumoto et al.			
(37 C.F.R. § 1.98(b))				Filing Date June 25, 2003		Group Art Unit 2828	
<b>Foreign Patent Documents or Published Foreign Patent Applications</b>							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes No
DPN	AY	4-307727	10/1992	Japan			

<b>Other Documents (include Author, Title, Date, and Place of Publication)</b>		
Examiner Initial	Desig. ID	Document
DPN	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; <i>MRS Symp. Proc.</i> 343; pp. 709; 1994
	AAA	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> 37-38; pp. 299-304; 1994
	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; <i>Appl. Surf. Sci.</i> 36; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; <i>IEEE IEDM</i> ; pp. 829-832; 1995
	AEE	Jhon et al.; "Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having a Gaussian Profile"; <i>Japan Journal of Applied Physics</i> , Vol. 33; pp. 1438-1441; October 1994
	AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; <i>Jpn. J. Appl. Phys</i> 33(10B); p. L1438; October 1994
	AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", <i>IEEE Transactions on Electron Devices</i> , Vol. 42, No. 2, pp. 251-257
	AHH	Kuriyama et al.; "Improving...ELA method for giant microelectronics"; <i>Jpn. J. Appl. Phys.</i> 31(12B); p. 4550; December 1992
	AII	Kuriyama et al.; "Lateral growth of Poly-Si films...by ELA..."; <i>Jpn. J. Appl. Phys.</i> 32(12B); p. 6190; December 1993
	AJJ	Okumura et al.; "Excimer laser annealed poly-Si TFT technologies"; <i>MRS Symp. Proc.</i> 377; p. 877; April 1995
DPN	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; <i>Optical Eng.</i> 31(2); p. 245; February 1992

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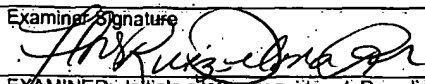
Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. <del>New Continuation</del> <del>Application</del> 0-602762
	Applicant Naoto Kusumoto et al.		
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SVA	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; <i>Optical Eng.</i> 31(2); p. 245; February 1992

Examiner Signature <i>Flora Ruth Delma</i>	Date Considered 10/04
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Substitute Form PTO-1449  
(Transmitted)U.S. Department of Commerce  
Patent and Trademark OfficeAttorney's Docket No.  
07977-004002Application No.  
10/602,762**Information Disclosure Statement  
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant  
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	AH						
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	AJ							
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<i>DPN</i>	AO	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> , Vol. 37-38; pp. 209-304; 1994

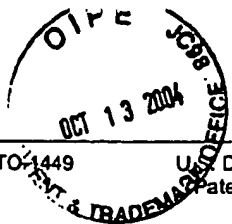
Examiner Signature

*Chris Ruiz*

Date Considered

12/02

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Sheet 1 of 1

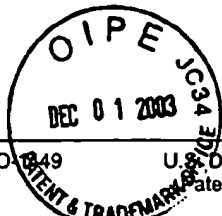
<b>Substitute Form PTO-1449</b> (Modified)  <b>Information Disclosure Statement</b> <b>by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>07977-004002</b>	Application No. <b>10/602,762</b>
	Applicant <b>Naoto Kusumoto et al.</b>		
	Filing Date <b>June 25, 2003</b>	Group Art Unit <b>2828</b>	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>DPA</i>	AA	2003/0015133	01/23/2003	ZHANG et al.			08/22/2002
	AB	2003/0207524	11/06/2003	ZHANG et al.			06/04/2003
	AC	5,352,291	10/04/1994	ZHANG et al.			08/11/1993
	AD	5,578,520	11/26/1996	ZHANG et al.			07/15/1994
	AE	5,766,344	06/16/1998	ZHANG et al.			05/26/1995
	AF	5,861,337	01/19/1999	ZHANG et al.			06/02/1995
	AG	6,174,374	01/16/2001	ZHANG et al.			09/26/1996
	AH	6,494,162	12/17/2002	ZHANG et al.			10/25/2000
	AI	6,576,534	06/10/2003	ZHANG et al.			02/10/1998
	AJ	6,770,143	08/03/2004	ZHANG et al.			08/22/2002
<i>SM</i>	AK						

Foreign Patent Documents or Published Foreign Patent Applications								
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							Yes	No
<i>DPA</i>	AL	JP05-182923	23 JUL 1993	JAPAN			Abstract	
<i>DPA</i>	AM	JP05-198507	06 AUG 1993	JAPAN			Abstract	
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)		
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	AT	

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<i>DFA</i>	AA	5,569,610	10/29/1996	Zhang et al.			03/08/1994
<i>DFA</i>	AB	5,614,733	03/25/1997	Zhang et al.			12/12/1994
<i>DFA</i>	AC	5,783,468	07/21/1998	Zhang et al.			04/10/1996
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<i>DFA</i>	AL	02-224346	09/06/1990	JAPAN			ABS	
<i>DFA</i>	AM	06-318701	11/15/1994	JAPAN			ABS	
<i>DFA</i>	AN	08-051074	02/20/1996	JAPAN			ABS	
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